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Zynq UltraScale+ MPSoC Data Sheet: DC and AC Switching Characteristics

DS925 (v1.3) April 20, 2017 **Preliminary Product Specification**

Summary

The Xilinx® Zynq® UltraScale+™ MPSoCs are available in -3, -2, -1 speed grades, with -3E devices having the highest performance. The -2LE and -1LI devices can operate at a V_{CCINT} voltage at 0.85V or 0.72V and are screened for lower maximum static power. When operated at V_{CCINT} = 0.85V, using -2LE and -1LI devices, the speed specification for the L devices is the same as the -2I or -1I speed grades. When operated at V_{CCINT} = 0.72V, the -2LE and -1LI performance and static and dynamic power is reduced.

DC and AC characteristics are specified in extended (E) and industrial (I) temperature ranges. Except the operating temperature range or unless otherwise noted, all the DC and AC electrical parameters are the same for a particular speed grade (that is, the timing characteristics of a -1 speed grade extended device are the same as for a -1 speed grade industrial device). However, only selected speed grades and/or devices are available in each temperature range.

All supply voltage and junction temperature specifications are representative of worst-case conditions. The parameters included are common to popular designs and typical applications.

This data sheet, part of an overall set of documentation on the Zynq UltraScale+ MPSoCs, is available on the Xilinx website at www.xilinx.com/documentation.

DC Characteristics

Absolute Maximum Ratings

Table 1: **Absolute Maximum Ratings(1)**

Symbol	Description	Min	Max	Units
Processor System (PS)				
$V_{CC\_PSINTFP}$	PS primary logic full-power domain supply voltage.	–0.500	1.000	V
$V_{CC\_PSINTLP}$	PS primary logic low-power domain supply voltage.	–0.500	1.000	V
V_{CC_PSAUX}	PS auxiliary supply voltage.	–0.500	2.000	V
$V_{CC\_PSINTFP\_DDR}$	PS DDR controller and PHY supply voltage.	–0.500	1.000	V
V_{CC_PSADC}	PS SYSMON ADC supply voltage relative to GND_PSADC.	–0.500	2.000	V
V_{CC_PSPLL}	PS PLL supply voltage.	–0.500	1.320	V
$V_{PS\_MGTRAVCC}$	PS-GTR supply voltage.	–0.500	1.000	V
$V_{PS\_MGTRAVTT}$	PS-GTR termination voltage.	–0.500	2.000	V
$V_{PS\_MGTREFCLK}$	PS-GTR reference clock input voltage.	–0.500	1.100	V
V_{PS_MGTRIN}	PS-GTR receiver input voltage.	–0.500	1.100	V

Table 1: **Absolute Maximum Ratings(1) *(Cont'd)***

Symbol	Description	Min	Max	Units
V_{CCO_PSDDR}	PS DDR I/O supply voltage.	–0.500	1.650	V
$V_{CC\_PSDDR\_PLL}$	PS DDR PLL supply voltage.	–0.500	2.000	V
V_{CCO_PSIO}	PS I/O supply.	–0.500	3.630	V
V_{PSIN}(2)	PS I/O input voltage.	–0.500	V_{CCO_PSIO} + 0.550	V
	PS DDR I/O input voltage.	–0.500	V_{CCO_PSDDR} + 0.550	V
V_{CC_PSBATT}	PS battery-backed RAM and battery-backed real-time clock (RTC) supply voltage.	–0.500	2.000	V
Programmable Logic (PL)				
V_{CCINT}	Internal supply voltage.	–0.500	1.000	V
V_{CCINT_IO}(3)	Internal supply voltage for the I/O banks.	–0.500	1.000	V
V_{CCAUX}	Auxiliary supply voltage.	–0.500	2.000	V
V_{CCBRAM}	Supply voltage for the block RAM memories.	–0.500	1.000	V
V_{CCO}	Output drivers supply voltage for HD I/O banks.	–0.500	3.400	V
	Output drivers supply voltage for HP I/O banks.	–0.500	2.000	V
V_{CCAUX_IO}(4)	Auxiliary supply voltage for the I/O banks.	–0.500	2.000	V
V_{REF}	Input reference voltage.	–0.500	2.000	V
V_{IN}(2)(5)(7)	I/O input voltage for HD I/O banks.(6)	–0.550	V_{CCO} + 0.550	V
	I/O input voltage for HP I/O banks.	–0.550	V_{CCO} + 0.550	V
I_{DC}	Available output current at the pad.	–20	20	mA
I_{RMS}	Available RMS output current at the pad.	–20	20	mA
GTH or GTY Transceiver				
$V_{MGTAVCC}$	Analog supply voltage for transceiver circuits.	–0.500	1.000	V
$V_{MGTAVTT}$	Analog supply voltage for transceiver termination circuits.	–0.500	1.300	V
$V_{MGTVCCAUX}$	Auxiliary analog Quad PLL (QPLL) voltage supply for transceivers.	–0.500	1.900	V
$V_{MGTREFCLK}$	Transceiver reference clock absolute input voltage.	–0.500	1.300	V
$V_{MGTAVTTRCAL}$	Analog supply voltage for the resistor calibration circuit of the transceiver column.	–0.500	1.300	V
V_{IN}	Receiver (RXP/RXN) and transmitter (TXP/TXN) absolute input voltage.	–0.500	1.200	V
$I_{DCIN-FLOAT}$	DC input current for receiver input pins DC coupled RX termination = floating.(8)	–	10	mA
$I_{DCIN-MGTAVTT}$	DC input current for receiver input pins DC coupled RX termination = $V_{MGTAVTT}$.	–	10	mA
$I_{DCIN-GND}$	DC input current for receiver input pins DC coupled RX termination = GND.(9)	–	0	mA
$I_{DCIN-PROG}$	DC input current for receiver input pins DC coupled RX termination = programmable.(10)	–	0	mA
$I_{DCOUT-FLOAT}$	DC output current for transmitter pins DC coupled RX termination = floating.	–	6	mA
$I_{DCOUT-MGTAVTT}$	DC output current for transmitter pins DC coupled RX termination = $V_{MGTAVTT}$.	–	6	mA

Table 1: **Absolute Maximum Ratings(1) *(Cont'd)***

Symbol	Description	Min	Max	Units
Video Codec Unit				
V_{CCINT_VCU}	Internal supply voltage for the video codec unit.	–0.500	1.000	V
PL System Monitor				
V_{CCADC}	PL System Monitor supply relative to GNDADC.	0.500	2.000	V
V_{REFP}	PL System Monitor reference input relative to GNDADC.	0.500	2.000	V
Temperature				
T_{STG}	Storage temperature (ambient).	–65	150	°C
T_{SOL}	Maximum soldering temperature.(12)	–	260	°C
T_j	Maximum junction temperature.(12)	–	125	°C

Notes:

1. Stresses beyond those listed under Absolute Maximum Ratings might cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time might affect device reliability.
2. When operating outside of the recommended operating conditions, refer to Table 6, Table 7, and Table 8 for maximum overshoot and undershoot specifications.
3. V_{CCINT_IO} must be connected to V_{CCBRAM}.
4. V_{CCAUX_IO} must be connected to V_{CCAUX}.
5. The lower absolute voltage specification always applies.
6. If V_{CCO} is 3.3V, the maximum voltage is 3.4V.
7. For I/O operation, see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).
8. AC coupled operation is not supported for RX termination = floating.
9. For GTY transceivers, DC coupled operation is not supported for RX termination = GND.
10. DC coupled operation is not supported for RX termination = programmable.
11. For more information on supported GTH or GTY transceiver terminations see the *UltraScale Architecture GTH Transceiver User Guide* (UG576) or *UltraScale Architecture GTY Transceiver User Guide* (UG578).
12. For soldering guidelines and thermal considerations, see the *Zynq UltraScale+ MPSoC Packaging and Pinout Specifications* (UG1075).

Recommended Operating Conditions

Table 2: **Recommended Operating Conditions(1)(2)**

Symbol	Description	Min	Typ	Max	Units
Processor System					
$V_{CC\_PSINTFP}$(3)	PS full-power domain supply voltage.	0.808	0.850	0.892	V
	For -1LI and -2LE (V_{CCINT} = 0.72V) devices: PS full-power domain supply voltage.	0.808	0.850	0.892	V
	For -3E devices: PS full-power domain supply voltage.	0.873	0.900	0.927	V
$V_{CC\_PSINTLP}$	PS low-power domain supply voltage.	0.808	0.850	0.892	V
	For -1LI and -2LE (V_{CCINT} = 0.72V) devices: PS low-power domain supply voltage.	0.808	0.850	0.892	V
	For -3E devices: PS low-power domain supply voltage.	0.873	0.900	0.927	V
V_{CC_PSAUX}	PS auxiliary supply voltage.	1.710	1.800	1.890	V
$V_{CC\_PSINTFP\_DDR}$(3)	PS DDR controller and PHY supply voltage.	0.808	0.850	0.892	V
	For -1LI and -2LE (V_{CCINT} = 0.72V) devices: PS DDR controller and PHY supply voltage.	0.808	0.850	0.892	V
	For -3E devices: PS DDR controller and PHY supply voltage.	0.873	0.900	0.927	V
V_{CC_PSADC}	PS SYSMON ADC supply voltage relative to GND_PSADC.	1.710	1.800	1.890	V
V_{CC_PSPLL}	PS PLL supply voltage.	1.164	1.200	1.236	V
$V_{PS\_MGTRAVCC}$	PS-GTR supply voltage.	0.825	0.850	0.875	V
$V_{PS\_MGTRAVTT}$	PS-GTR termination voltage.	1.746	1.800	1.854	V
V_{CCO_PSDDR}(4)	PS DDR I/O supply voltage.	1.06	–	1.575	V
$V_{CC\_PSDDR\_PLL}$	PS DDR PLL supply voltage.	1.710	1.800	1.890	V
V_{CCO_PSIO}(5)	PS I/O supply.	1.710	–	3.465	V
V_{PSIN}	PS I/O input voltage.	–0.200	–	V_{CCO_PSIO} + 0.200	V
	PS DDR I/O input voltage.	–0.200	–	V_{CCO_PSDDR} + 0.200	
V_{CC_PSBATT}(6)	PS battery-backed RAM and battery-backed real-time clock (RTC) supply voltage.	1.200	–	1.500	V
Programmable Logic					
V_{CCINT}	PL internal supply voltage.	0.825	0.850	0.876	V
	For -1LI and -2LE (V_{CCINT} = 0.72V) devices: PL internal supply voltage.	0.698	0.720	0.742	V
	For -3E devices: PL internal supply voltage.	0.873	0.900	0.927	V
V_{CCINT_IO}(7)	PL internal supply voltage for the I/O banks.	0.825	0.850	0.876	V
	For -1LI and -2LE (V_{CCINT} = 0.72V) devices: PL internal supply voltage for the I/O banks.	0.825	0.850	0.876	V
	For -3E devices: PL internal supply voltage for the I/O banks.	0.873	0.900	0.927	V
V_{CCBRAM}	Block RAM supply voltage.	0.825	0.850	0.876	V
	For -3E devices: block RAM supply voltage.	0.873	0.900	0.927	V
V_{CCAUX}	Auxiliary supply voltage.	1.746	1.800	1.854	V

Table 2: **Recommended Operating Conditions(1)(2) *(Cont'd)***

Symbol	Description	Min	Typ	Max	Units
V_{CCO}(8)	Supply voltage for HD I/O banks.	1.140	–	3.400	V
	Supply voltage for HP I/O banks.	0.950	–	1.900	V
V_{CCAUX_IO}(9)	Auxiliary I/O supply voltage.	1.746	1.800	1.854	V
V_{IN}(10)	I/O input voltage.	–0.200	–	V_{CCO} + 0.200	V
I_{IN}(11)	Maximum current through any PL or PS pin in a powered or unpowered bank when forward biasing the clamp diode.	–	–	10	mA
GTH or GTY Transceiver					
$V_{MGTAVCC}$(12)	Analog supply voltage for the GTH or GTY transceiver.	0.873	0.900	0.927	V
$V_{MGTAVTT}$(12)	Analog supply voltage for the GTH or GTY transmitter and receiver termination circuits.	1.164	1.200	1.236	V
$V_{MGTVCCAUX}$(12)	Auxiliary analog QPLL voltage supply for the transceivers.	1.746	1.800	1.854	V
$V_{MGTAVTTRCAL}$(12)	Analog supply voltage for the resistor calibration circuit of the GTH or GTY transceiver column.	1.164	1.200	1.236	V
VCU					
V_{CCINT_VCU}	Internal supply voltage for the VCU.	0.825	0.850	0.876	V
	For -1LI and -2LE (V_{CCINT} = 0.72V) devices: Internal supply voltage for the VCU.	0.825	0.850	0.876	V
	For -3E devices: Internal supply voltage for the VCU.	0.873	0.900	0.927	V

Table 2: **Recommended Operating Conditions(1)(2) *(Cont'd)***

Symbol	Description	Min	Typ	Max	Units
PL System Monitor					
V_{CCADC}	PL System Monitor supply relative to GNDADC.	1.746	1.800	1.854	V
V_{REFP}	PL System Monitor externally supplied reference voltage relative to GNDADC.	1.200	1.250	1.300	V
Temperature					
T_j(13)	Junction temperature operating range for extended (E) temperature devices.(14)	0	–	100	°C
	Junction temperature operating range for industrial (I) temperature devices.	–40	–	100	°C
	Junction temperature operating range for eFUSE programming.	–40	–	125	°C

Notes:

1. All voltages are relative to GND.
2. For the design of the power distribution system consult *UltraScale Architecture PCB Design Guide* (UG583).
3. $V_{CC\_PSINTFP\_DDR}$ must be tied to $V_{CC\_PSINTFP}$.
4. Includes V_{CCO_PSDDR} of 1.2V, 1.35V, 1.5V at ±5% and 1.1V +0.07V/–0.04V depending upon the tolerances required by specific memory standards.
5. Applies to all PS I/O supply banks. Includes V_{CCO_PSIO} of 1.8V, 2.5V, and 3.3V at ±5%.
6. If the battery-backed RAM or RTC is not used, connect V_{CC_PSBATT} to GND or V_{CC_PSAUX}. The V_{CC_PSAUX} maximum of 1.89V is acceptable on an unused V_{CC_PSBATT}.
7. V_{CCINT_IO} must be connected to V_{CCBRAM}.
8. Includes V_{CCO} of 1.0V (HP I/O only), 1.2V, 1.35V, 1.5V, 1.8V, 2.5V (HD I/O only) at ±5%, and 3.3V (HD I/O only) at +3/–5%.
9. V_{CCAUX_IO} must be connected to V_{CCAUX}.
10. The lower absolute voltage specification always applies.
11. A total of 200 mA per bank should not be exceeded.
12. Each voltage listed requires filtering as described in *UltraScale Architecture GTH Transceiver User Guide* (UG576) or *UltraScale Architecture GTY Transceiver User Guide* (UG578).
13. Xilinx recommends measuring the Tj of a device using the system monitor as described in the *UltraScale Architecture System Monitor User Guide* (UG580). The SYSMON temperature measurement errors (that are described in Table 69 and Table 124) must be accounted for in your design. For example, when using the PL system monitor with an external reference of 1.25V, when SYSMON reports 97°C, there is a measurement error ±3°C. A reading of 97°C is considered the maximum adjusted Tj (100°C – 3°C = 97°C).
14. Devices labeled with the speed/temperature grade of -2LE normally operate under Extended (E) temperature grade specifications with a maximum junction temperature of 100°C. However, E temperature grade devices can operate for a limited time at a junction temperature of 110°C. Timing parameters adhere to the same speed file at 110°C as they do at 100°C, regardless of operating voltage (nominal voltage of 0.85V or a low-voltage of 0.72V). Operation at Tj = 110°C is limited to 1% of the device lifetime and can occur sequentially or at regular intervals as long as the total time does not exceed 1% of the device lifetime.

Available Speed Grades and Operating Voltages

Table 3 describes the speed grades per device and the V_{CCINT} operating supply voltages for the full-power, low-power, and DDR domains. For more information on selecting devices and speed grades, see the *UltraScale Architecture and Product Overview* (DS890).

Table 3: **Available Speed Grades and Operating Voltages**

Speed Grade	V_{CCINT}	$V_{CC\_PSINTLP}$	$V_{CC\_PSINTFP}$	$V_{CC\_PSINTFP\_DDR}$	Units
-3E	0.90	0.90	0.90	0.90	V
-2E	0.85	0.85	0.85	0.85	V
-2I	0.85	0.85	0.85	0.85	V
-2LE	0.85	0.85	0.85	0.85	V
-1E	0.85	0.85	0.85	0.85	V
-1I	0.85	0.85	0.85	0.85	V
-1LI	0.85	0.85	0.85	0.85	V
-2LE	0.72	0.85	0.85	0.85	V
-1LI	0.72	0.85	0.85	0.85	V

DC Characteristics Over Recommended Operating Conditions

Table 4: **DC Characteristics Over Recommended Operating Conditions**

Symbol	Description	Min	Typ(1)	Max	Units
V_{DRINT}	Data retention V_{CCINT} voltage (below which configuration data might be lost).	0.68	–	–	V
V_{DRAUX}	Data retention V_{CCAUX} voltage (below which configuration data might be lost).	1.5	–	–	V
I_{REF}	V_{REF} leakage current per pin.	–	–	15	µA
I_L	Input or output leakage current per pin (sample-tested).(2)	–	–	15	µA
C_{IN}(3)	Die input capacitance at the pad (HP I/O).	–	–	3.1	pF
	Die input capacitance at the pad (HD I/O).	–	–	4.75	pF
I_{RPU}	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 3.3V.	75	–	190	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 2.5V.	50	–	169	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.8V.	60	–	120	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.5V.	30	–	120	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.2V.	10	–	100	µA
I_{RPD}	Pad pull-down (when selected) at V_{IN} = 3.3V.	60	–	200	µA
	Pad pull-down (when selected) at V_{IN} = 1.8V.	29	–	120	µA
$I_{CCADCONPL}$	Analog supply current for the PL SYSMON circuits in the power-up state.	–	–	8	mA
$I_{CCADCONPS}$	Analog supply current for the PS SYSMON circuits in the power-up state.	–	–	10	mA
$I_{CCADCOFFPL}$	Analog supply current for the PL SYSMON circuits in the power-down state.	–	–	1.5	mA
$I_{CCADCOFFPS}$	Analog supply current for the PS SYSMON circuits in the power-down state.	–	–	1.8	mA

Table 4: **DC Characteristics Over Recommended Operating Conditions *(Cont'd)***

Symbol	Description	Min	Typ(1)	Max	Units
I_{CC_PSBATT}(4)(5)	Battery supply current at V_{CC_PSBATT} = 1.50V, RTC enabled.	–	–	3650	nA
	Battery supply current at V_{CC_PSBATT} = 1.50V, RTC disabled.	–	–	650	nA
	Battery supply current at V_{CC_PSBATT} = 1.20V, RTC enabled.	–	–	3150	nA
	Battery supply current at V_{CC_PSBATT} = 1.20V, RTC disabled.	–	–	150	nA
I_{PSFS}(6)	PS V_{CC_PSAUX} additional supply current during eFUSE programming.	–	–	115	mA
Calibrated programmable on-die termination (DCI) in HP I/O banks(8) (measured per JEDEC specification)					
R(9)	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_40.	–10%(7)	40	+10%(7)	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_48.	–10%(7)	48	+10%(7)	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_60.	–10%(7)	60	+10%(7)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_40.	–10%(7)	40	+10%(7)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_48.	–10%(7)	48	+10%(7)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_60.	–10%(7)	60	+10%(7)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_120.	–10%(7)	120	+10%(7)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_240.	–10%(7)	240	+10%(7)	Ω
Uncalibrated programmable on-die termination in HP I/Os banks (measured per JEDEC specification)					
R(9)	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_40.	–50%	40	+50%	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_48.	–50%	48	+50%	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_60.	–50%	60	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_40.	–50%	40	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_48.	–50%	48	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_60.	–50%	60	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_120.	–50%	120	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_240.	–50%	240	+50%	Ω
Uncalibrated programmable on-die termination in HD I/O banks (measured per JEDEC specification)					
R(9)	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_48.	–50%	48	+50%	Ω
Internal V_{REF}	50% V_{CCO}	V_{CCO} x 0.49	V_{CCO} x 0.50	V_{CCO} x 0.51	V
	70% V_{CCO}	V_{CCO} x 0.69	V_{CCO} x 0.70	V_{CCO} x 0.71	V

Table 4: **DC Characteristics Over Recommended Operating Conditions *(Cont'd)***

Symbol	Description	Min	Typ(1)	Max	Units
Differential termination	Programmable differential termination (TERM_100) for HP I/O banks.	–35%	100	+35%	Ω
n	Temperature diode ideality factor.	–	1.026	–	–
r	Temperature diode series resistance.	–	2	–	Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. For HP I/O banks with a V_{CCO} of 1.8V and separated V_{CCO} and V_{CCAUX_IO} power supplies, the I_L maximum current is 70 µA.
3. This measurement represents the die capacitance at the pad, not including the package.
4. Maximum value specified for worst case process at 25°C.
5. I_{CC_PSBATT} is measured when the battery-backed RAM (BBRAM) is enabled.
6. Do not program eFUSE during device configuration (e.g., during configuration, during configuration readback, or when readback CRC is active).
7. If VRP resides at a different bank (DCI cascade), the range increases to ±15%.
8. VRP resistor tolerance is (240Ω ±1%)
9. On-die input termination resistance, for more information see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).

Table 5: **PS MIO Pull-up and Pull-down Current**

Symbol	Description	Min	Max	Units
I_{RPU}	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO_PSMIO} = 3.3V.	20	80	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO_PSMIO} = 2.5V.	20	80	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO_PSMIO} = 1.8V.	15	65	µA
I_{RPD}	Pad pull-down (when selected) at V_{IN} = 3.3V.	20	80	µA
	Pad pull-down (when selected) at V_{IN} = 2.5V.	20	80	µA
	Pad pull-down (when selected) at V_{IN} = 1.8V.	15	65	µA

V_{IN} Maximum Allowed AC Voltage Overshoot and Undershoot

Table 6: **V_{IN} Maximum Allowed AC Voltage Overshoot and Undershoot for HD I/O Banks(1)**

AC Voltage Overshoot	% of UI at –40°C to 100°C	AC Voltage Undershoot	% of UI at –40°C to 100°C
V_{CCO} + 0.30	100%	–0.30	100%
V_{CCO} + 0.35	100%	–0.35	90%
V_{CCO} + 0.40	100%	–0.40	78%
V_{CCO} + 0.45	100%	–0.45	40%
V_{CCO} + 0.50	100%	–0.50	24%
V_{CCO} + 0.55	100%	–0.55	18.0%
V_{CCO} + 0.60	100%	–0.60	13.0%
V_{CCO} + 0.65	100%	–0.65	10.8%
V_{CCO} + 0.70	92%	–0.70	9.0%
V_{CCO} + 0.75	92%	–0.75	7.0%
V_{CCO} + 0.80	92%	–0.80	6.0%
V_{CCO} + 0.85	92%	–0.85	5.0%
V_{CCO} + 0.90	92%	–0.90	4.0%
V_{CCO} + 0.95	92%	–0.95	2.5%

Notes:

1. A total of 200 mA per bank should not be exceeded.

Table 7: **V_{IN} Maximum Allowed AC Voltage Overshoot and Undershoot for HP I/O Banks(1)(2)**

AC Voltage Overshoot	% of UI at –40°C to 100°C	AC Voltage Undershoot	% of UI at –40°C to 100°C
V_{CCO} + 0.30	100%	–0.30	100%
V_{CCO} + 0.35	100%	–0.35	100%
V_{CCO} + 0.40	92%	–0.40	92%
V_{CCO} + 0.45	50%	–0.45	50%
V_{CCO} + 0.50	20%	–0.50	20%
V_{CCO} + 0.55	10%	–0.55	10%
V_{CCO} + 0.60	6%	–0.60	6%
V_{CCO} + 0.65	2%	–0.65	2%
V_{CCO} + 0.70	2%	–0.70	2%

Notes:

1. A total of 200 mA per bank should not be exceeded.
2. For UI smaller than 20 µs.

Table 8: **V_{PSIN} Maximum Allowed AC Voltage Overshoot and Undershoot for PS I/O Banks(1)**

AC Voltage Overshoot	% of UI at –40°C to 100°C	AC Voltage Undershoot	% of UI at –40°C to 100°C
V_{CCO_PSIO} + 0.30	100%	–0.30	100%
V_{CCO_PSIO} + 0.35	100%	–0.35	75%
V_{CCO_PSIO} + 0.40	100%	–0.40	45%
V_{CCO_PSIO} + 0.45	100%	–0.45	40%
V_{CCO_PSIO} + 0.50	75%	–0.50	10%
V_{CCO_PSIO} + 0.55	75%	–0.55	6%
V_{CCO_PSIO} + 0.60	60%	–0.60	2%
V_{CCO_PSIO} + 0.65	30%	–0.65	0%
V_{CCO_PSIO} + 0.70	20%	–0.70	0%
V_{CCO_PSIO} + 0.75	10%	–0.75	0%
V_{CCO_PSIO} + 0.80	10%	–0.80	0%
V_{CCO_PSIO} + 0.85	8%	–0.85	0%
V_{CCO_PSIO} + 0.90	6%	–0.90	0%
V_{CCO_PSIO} + 0.95	6%	–0.95	0%

Notes:

1. A total of 200 mA per bank should not be exceeded.

Quiescent Supply Current

Table 9: **Typical Quiescent Supply Current(1)(2)(3)(4)**

Symbol	Description	Device	Speed Grade and V_{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
I_{CCINTQ}	Quiescent V_{CCINT} supply current.	XCZU2	N/A	393	393	344	344	mA
		XCZU3	N/A	393	393	344	344	mA
		XCZU4	719	684	684	601	601	mA
		XCZU5	719	684	684	601	601	mA
		XCZU6	1629	1549	1549	1358	1358	mA
		XCZU7	1263	1201	1201	1055	1055	mA
		XCZU9	1629	1549	1549	1358	1358	mA
		XCZU11	1786	1699	1699	1491	1491	mA
		XCZU15	1987	1890	1890	1660	1660	mA
		XCZU17	2728	2594	2594	2275	2275	mA
		XCZU19	2728	2594	2594	2275	2275	mA
I_{CCINT_IOQ}	Quiescent V_{CCINT_IO} supply current.	XCZU2	N/A	44	44	44	44	mA
		XCZU3	N/A	44	44	44	44	mA
		XCZU4	61	59	59	59	59	mA
		XCZU5	61	59	59	59	59	mA
		XCZU6	61	59	59	59	59	mA
		XCZU7	120	115	115	115	115	mA
		XCZU9	61	59	59	59	59	mA
		XCZU11	120	115	115	115	115	mA
		XCZU15	61	59	59	59	59	mA
		XCZU17	164	158	158	158	158	mA
		XCZU19	164	158	158	158	158	mA
I_{CCOQ}	Quiescent V_{CCO} supply current.	All devices	1	1	1	1	1	mA
I_{CCAUXQ}	Quiescent V_{CCAUX} supply current.	XCZU2	N/A	55	55	55	55	mA
		XCZU3	N/A	55	55	55	55	mA
		XCZU4	90	90	90	90	90	mA
		XCZU5	90	90	90	90	90	mA
		XCZU6	227	227	227	227	227	mA
		XCZU7	174	174	174	174	174	mA
		XCZU9	227	227	227	227	227	mA
		XCZU11	255	255	255	255	255	mA
		XCZU15	266	266	266	266	266	mA
		XCZU17	396	396	396	396	396	mA
		XCZU19	396	396	396	396	396	mA

Table 9: **Typical Quiescent Supply Current(1)(2)(3)(4) *(Cont'd)***

Symbol	Description	Device	Speed Grade and V_{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
I_{CCAUX_IOQ}	Quiescent V_{CCAUX_IO} supply current.	XCZU2	N/A	26	26	26	26	mA
		XCZU3	N/A	26	26	26	26	mA
		XCZU4	32	32	32	32	32	mA
		XCZU5	32	32	32	32	32	mA
		XCZU6	33	33	33	33	33	mA
		XCZU7	56	56	56	56	56	mA
		XCZU9	33	33	33	33	33	mA
		XCZU11	56	56	56	56	56	mA
		XCZU15	33	33	33	33	33	mA
		XCZU17	74	74	74	74	74	mA
		XCZU19	74	74	74	74	74	mA
$I_{CCBRAMQ}$	Quiescent V_{CCBRAM} supply current.	XCZU2	N/A	6	6	6	6	mA
		XCZU3	N/A	6	6	6	6	mA
		XCZU4	9	9	9	9	9	mA
		XCZU5	9	9	9	9	9	mA
		XCZU6	25	24	24	24	24	mA
		XCZU7	16	15	15	15	15	mA
		XCZU9	25	24	24	24	24	mA
		XCZU11	23	22	22	22	22	mA
		XCZU15	29	28	28	28	28	mA
		XCZU17	37	35	35	35	35	mA
		XCZU19	37	35	35	35	35	mA

Notes:

1. Typical values are specified at nominal voltage, 85°C junction temperatures (T_j) with single-ended SelectIO™ resources.
2. Typical values are for blank configured devices with no output current loads, no active input pull-up resistors, all I/O pins are 3-state and floating.
3. Use the Xilinx Power Estimator (XPE) spreadsheet tool (download at www.xilinx.com/power) to estimate static power consumption for conditions or supplies other than those specified.
4. Typical values depend upon your configuration. To accurately estimate all PS supply currents, use the interactive XPE spreadsheet tool.

Power Supply Sequencing

PS Power-On/Off Power Supply Sequencing

The low-power domain (LPD) must operate before the full-power domain (FPD) can function. The low-power and full-power domains can be powered simultaneously. The PS_POR_B input must be asserted to GND during the power-on sequence (see Table 37). The FPD (when used) must be powered before PS_POR_B is released.

To achieve minimum current draw and ensure that the I/Os are 3-stated at power-on, the recommended power-on sequence for the low-power domain (LPD) is listed. The recommended power-off sequence is the reverse of the power-on sequence.

1. $V_{CC\_PSINTLP}$
2. V_{CC_PSAUX}, V_{CC_PSADC}, and V_{CC_PSPLL} in any order or simultaneously.
3. V_{CCO_PSIO}

To achieve minimum current draw and ensure that the I/Os are 3-stated at power-on, the recommended power-on sequence for the full-power domain (FPD) is listed. The recommended power-off sequence is the reverse of the power-on sequence.

1. $V_{CC\_PSINTFP}$ and $V_{CC\_PSINTFP\_DDR}$ driven from the same supply source.
2. $V_{PS\_MGTRAVCC}$ and $V_{CC\_PSDDR\_PLL}$ in any order or simultaneously.
3. $V_{PS\_MGTRAVTT}$ and V_{CCO_PSDDR} in any order or simultaneously.

PL Power-On/Off Power Supply Sequencing

The recommended power-on sequence is V_{CCINT}, V_{CCINT_IO}/V_{CCBRAM}/V_{CCINT_VCU}, V_{CCAUX}/V_{CCAUX_IO}, and V_{CCO} to achieve minimum current draw and ensure that the I/Os are 3-stated at power-on. The recommended power-off sequence is the reverse of the power-on sequence. If V_{CCINT} and V_{CCINT_IO}/V_{CCBRAM} have the same recommended voltage levels, they can be powered by the same supply and ramped simultaneously. V_{CCINT_IO} must be connected to V_{CCBRAM}. If V_{CCAUX}/V_{CCAUX_IO} and V_{CCO} have the same recommended voltage levels, they can be powered by the same supply and ramped simultaneously. V_{CCAUX} and V_{CCAUX_IO} must be connected together. V_{CCADC} and V_{REF} can be powered at any time and have no power-up sequencing requirements.

The recommended power-on sequence to achieve minimum current draw for the GTH or GTY transceivers is V_{CCINT}, $V_{MGTAVCC}$, $V_{MGTAVTT}$ OR $V_{MGTAVCC}$, V_{CCINT}, $V_{MGTAVTT}$. There is no recommended sequencing for $V_{MGTVCCAUX}$. Both $V_{MGTAVCC}$ and V_{CCINT} can be ramped simultaneously. The recommended power-off sequence is the reverse of the power-on sequence to achieve minimum current draw.

If these recommended sequences are not met, current drawn from $V_{MGTAVTT}$ can be higher than specifications during power-up and power-down.

PS-PL Power Sequencing

The PS and PL power supplies are fully independent. All PS power supplies can be powered before or after any PL power supplies. The PS and PL power regions are isolated to prevent damage.

Power Supply Requirements

Table 10 shows the minimum current, in addition to I_{CCQ} maximum, required by each Zynq UltraScale+ device for proper power-on and configuration. If the current minimums shown in Table 10 are met, the device powers on after all supplies have passed through their power-on reset threshold voltages. The device must not be configured until after V_{CCINT} is applied. Once initialized and configured, use the Xilinx Power Estimator (XPE) tools to estimate current drain on these supplies.

Table 10: **Power-on Current by Device(1)**

I_{CC} Min =	I_{CCQ} +	XCZU2	XCZU3	XCZU4	XCZU5	XCZU6	XCZU7	XCZU9	XCZU11	XCZU15	XCZU17	XCZU19	Units
$I_{CCINTMIN}$	I_{CCINTQ}+	464	464	770	770	1800	1514	1800	1961	2242	3433	3433	mA
I_{CCINT_IOMIN}+ $I_{CCBRAMMIN}$	$I_{CCBRAMQ}$+ I_{CCINT_IOQ}+	155	155	257	257	600	505	600	654	748	1145	1145	mA
I_{CCOMIN}	I_{CCOQ}+	50	50	50	50	50	50	50	55	63	96	96	mA
$I_{CCAUXMIN}$+ I_{CCAUX_IOMIN}	I_{CCAUXQ}+ I_{CCAUX_IOQ}+	111	111	386	386	650	362	650	709	810	1240	1240	mA

Notes:

1. Use the Xilinx Power Estimator (XPE) spreadsheet tool (download at www.xilinx.com/power) to estimate power-on current for all supplies.

Table 11 shows the power supply ramp time.

Table 11: **Power Supply Ramp Time**

Symbol	Description	Min	Max	Units
T_{VCCINT}	Ramp time from GND to 95% of V_{CCINT}.	0.2	40	ms
T_{VCCINT_IO}	Ramp time from GND to 95% of V_{CCINT_IO}.	0.2	40	ms
T_{VCCINT_VCU}	Ramp time from GND to 95% of V_{CCINT_VCU}.	0.2	40	ms
T_{VCCO}	Ramp time from GND to 95% of V_{CCO}.	0.2	40	ms
T_{VCCAUX}	Ramp time from GND to 95% of V_{CCAUX}.	0.2	40	ms
$T_{VCCBRAM}$	Ramp time from GND to 95% of V_{CCBRAM}.	0.2	40	ms
$T_{MGTAVCC}$	Ramp time from GND to 95% of $V_{MGTAVCC}$.	0.2	40	ms
$T_{MGTAVTT}$	Ramp time from GND to 95% of $V_{MGTAVTT}$.	0.2	40	ms
$T_{MGTVCCAUX}$	Ramp time from GND to 95% of $V_{MGTVCCAUX}$.	0.2	40	ms
$T_{VCC\_PSINTFP}$	Ramp time from GND to 95% of $V_{CC\_PSINTFP}$.	0.2	40	ms
$T_{VCC\_PSINTLP}$	Ramp time from GND to 95% of $V_{CC\_PSINTLP}$.	0.2	40	ms
T_{VCC_PSAUX}	Ramp time from GND to 95% of V_{CC_PSAUX}.	0.2	40	ms
$T_{VCC\_PSINTFP\_DDR}$	Ramp time from GND to 95% of $V_{CC\_PSINTFP\_DDR}$.	0.2	40	ms
T_{VCC_PSADC}	Ramp time from GND to 95% of V_{CC_PSADC}.	0.2	40	ms
T_{VCC_PSPLL}	Ramp time from GND to 95% of V_{CC_PSPLL}.	0.2	40	ms
$T_{PS\_MGTRAVCC}$	Ramp time from GND to 95% of $V_{CC\_MGTRAVCC}$.	0.2	40	ms
$T_{PS\_MGTRAVTT}$	Ramp time from GND to 95% of $V_{CC\_MGTRAVTT}$.	0.2	40	ms

Table 11: **Power Supply Ramp Time *(Cont'd)***

Symbol	Description	Min	Max	Units
T_{VCCO_PSDDR}	Ramp time from GND to 95% of V_{CCO_PSDDR}.	0.2	40	ms
$T_{VCC\_PSDDR\_PLL}$	Ramp time from GND to 95% of $V_{CC\_PSDDR\_PLL}$.	0.2	40	ms
T_{VCCO_PSIO}	Ramp time from GND to 95% of V_{CCO_PSIO}.	0.2	40	ms

DC Input and Output Levels

Values for V_{IL} and V_{IH} are recommended input voltages. Values for I_{OL} and I_{OH} are guaranteed over the recommended operating conditions at the V_{OL} and V_{OH} test points. Only selected standards are tested. These are chosen to ensure that all standards meet their specifications. The selected standards are tested at a minimum V_{CCO} with the respective V_{OL} and V_{OH} voltage levels shown. Other standards are sample tested.

PS I/O Levels

Table 12: **PS MIO and CONFIG DC Input and Output Levels(1)**

I/O Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
LVCMOS33	–0.300	0.800	2.000	V_{CCO_PSIO}	0.40	2.40	12	–12
LVCMOS25	–0.300	0.700	1.700	V_{CCO_PSIO} + 0.30	0.70	1.70	12	–12
LVCMOS18	–0.300	35% V_{CCO_PSIO}	65% V_{CCO_PSIO}	V_{CCO_PSIO} + 0.30	0.45	V_{CCO_PSIO} – 0.45	12	–12

Notes:
1. Tested according to relevant specifications.

Table 13: **PS DDR DC Input and Output Levels(1)**

DDR Standard	V_{IL}		V_{IH}		V_{OL}(2)	V_{OH}(2)	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
DDR4	0.000	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO_PSDDR}	0.8 x V_{CCO_PSDDR} – 0.150	0.8 x V_{CCO_PSDDR} + 0.150	10	–0.1
LPDDR4	0.000	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO_PSDDR}	0.3 x V_{CCO_PSDDR} – 0.150	0.3 x V_{CCO_PSDDR} + 0.150	0.1	–10
DDR3	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO_PSDDR}	0.5 x V_{CCO_PSDDR} – 0.175	0.5 x V_{CCO_PSDDR} + 0.175	8	–8
LPDDR3	0.000	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO_PSDDR}	0.5 x V_{CCO_PSDDR} – 0.150	0.5 x V_{CCO_PSDDR} + 0.150	8	–8
DDR3L	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO_PSDDR}	0.5 x V_{CCO_PSDDR} – 0.150	0.5 x V_{CCO_PSDDR} + 0.150	8	–8

Notes:
1. Tested according to relevant specifications.
2. DDR4 V_{OL}/V_{OH} specifications are only applicable for DQ/DQS pins.

PL I/O Levels

Table 14: **SelectIO DC Input and Output Levels For HD I/O Banks(1)(2)(3)**

I/O Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
HSTL_I	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	8.0	–8.0
HSTL_I_18	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	8.0	–8.0
HSUL_12	–0.300	V_{REF} – 0.130	V_{REF} + 0.130	V_{CCO} + 0.300	20% V_{CCO}	80% V_{CCO}	0.1	–0.1
LVCMOS12	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	Note 4	Note 4
LVCMOS15	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} – 0.450	Note 5	Note 5
LVCMOS18	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} – 0.450	Note 5	Note 5
LVCMOS25	–0.300	0.700	1.700	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	Note 5	Note 5
LVCMOS33	–0.300	0.800	2.000	3.400	0.400	V_{CCO} – 0.400	Note 5	Note 5
LVTTL	–0.300	0.800	2.000	3.400	0.400	2.400	Note 5	Note 5
SSTL12	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	14.25	–14.25
SSTL135	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	8.9	–8.9
SSTL135_II	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	13.0	–13.0
SSTL15	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.175	V_{CCO}/2 + 0.175	8.9	–8.9
SSTL15_II	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.175	V_{CCO}/2 + 0.175	13.0	–13.0
SSTL18_I	–0.300	V_{REF} – 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	V_{CCO}/2 – 0.470	V_{CCO}/2 + 0.470	8.0	–8.0
SSTL18_II	–0.300	V_{REF} – 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	V_{CCO}/2 – 0.600	V_{CCO}/2 + 0.600	13.4	–13.4
MIPI_DPHY_DCI_LP(6)	–0.300	0.550	0.880	V_{CCO} + 0.300	0.050	1.100	0.01	–0.01

Notes:

1. Tested according to relevant specifications.
2. Standards specified using the default I/O standard configuration. For details, see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).
3. POD10 and POD12 DC input and output levels are shown in Table 16, Table 20, Table 21, and Table 22.
4. Supported drive strengths of 4, 8, or 12 mA in HD I/O banks.
5. Supported drive strengths of 4, 8, 12, or 16 mA in HD I/O banks.
6. Low-power option for MIPI_DPHY_DCI.

Table 15: **SelectIO DC Input and Output Levels for HP I/O Banks(1)(2)(3)**

I/O Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
HSTL_I	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	5.8	–5.8
HSTL_I_12	–0.300	V_{REF} – 0.080	V_{REF} + 0.080	V_{CCO} + 0.300	25% V_{CCO}	75% V_{CCO}	4.1	–4.1
HSTL_I_18	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	6.2	–6.2
HSUL_12	–0.300	V_{REF} – 0.130	V_{REF} + 0.130	V_{CCO} + 0.300	20% V_{CCO}	80% V_{CCO}	0.1	–0.1
LVCMOS12	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	Note 4	Note 4
LVCMOS15	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} – 0.450	Note 5	Note 5
LVCMOS18	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} – 0.450	Note 5	Note 5
LVDCI_15	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} – 0.450	7.0	–7.0
LVDCI_18	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} – 0.450	7.0	–7.0
SSTL12	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	$V_{CCO}/2$ – 0.150	$V_{CCO}/2$ + 0.150	8.0	–8.0
SSTL135	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	$V_{CCO}/2$ – 0.150	$V_{CCO}/2$ + 0.150	9.0	–9.0
SSTL15	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	$V_{CCO}/2$ – 0.175	$V_{CCO}/2$ + 0.175	10.0	–10.0
SSTL18_I	–0.300	V_{REF} – 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	$V_{CCO}/2$ – 0.470	$V_{CCO}/2$ + 0.470	7.0	–7.0
MIPI_DPHY_DCI_LP(6)	–0.300	0.550	0.880	V_{CCO} + 0.300	0.050	1.100	0.01	–0.01

Notes:

1. Tested according to relevant specifications.
2. Standards specified using the default I/O standard configuration. For details, see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).
3. POD10 and POD12 DC input and output levels are shown in Table 16, Table 20, Table 21, and Table 22.
4. Supported drive strengths of 2, 4, 6, or 8 mA in HP I/O banks.
5. Supported drive strengths of 2, 4, 6, 8, or 12 mA in HP I/O banks.
6. Low-power option for MIPI_DPHY_DCI.

Table 16: **DC Input Levels for Single-ended POD10 and POD12 I/O Standards(1)(2)**

I/O Standard	V_{IL}		V_{IH}	
	V, Min	V, Max	V, Min	V, Max
POD10	–0.300	V_{REF} – 0.068	V_{REF} + 0.068	V_{CCO} + 0.300
POD12	–0.300	V_{REF} – 0.068	V_{REF} + 0.068	V_{CCO} + 0.300

Notes:

1. Tested according to relevant specifications.
2. Standards specified using the default I/O standard configuration. For details, see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).

Table 17: **Differential SelectIO DC Input and Output Levels**

I/O Standard	V_{ICM} (V)(1)			V_{ID} (V)(2)			V_{ILHS}(3)	V_{IHHS}(3)	V_{OCM} (V)(4)			V_{OD} (V)(5)		
	Min	Typ	Max	Min	Typ	Max	Min	Max	Min	Typ	Max	Min	Typ	Max
SUB_LVDS(8)	0.500	0.900	1.300	0.070	–	–	–	–	0.700	0.900	1.100	0.100	0.150	0.200
LVPECL	0.300	1.200	1.425	0.100	0.350	0.600	–	–	–	–	–	–	–	–
SLVS_400_18	0.070	0.200	0.330	0.140	–	0.450	–	–	–	–	–	–	–	–
SLVS_400_25	0.070	0.200	0.330	0.140	–	0.450	–	–	–	–	–	–	–	–
MIPI_DPHY_DCI_HS(9)	0.070	–	0.330	0.070	–	–	–0.040	0.460	0.150	0.200	0.250	0.140	0.200	0.270

Notes:

1. V_{ICM} is the input common mode voltage.
2. V_{ID} is the input differential voltage (Q – $\overline{Q}$).
3. V_{IHHS} and V_{ILHS} are the single-ended input high and low voltages, respectively.
4. V_{OCM} is the output common mode voltage.
5. V_{OD} is the output differential voltage (Q – $\overline{Q}$).
6. LVDS_25 is specified in Table 23.
7. LVDS is specified in Table 24.
8. Only the SUB_LVDS receiver is supported in HD I/O banks.
9. High-speed option for MIPI_DPHY_DCI. The V_{ID} maximum is aligned with the standard's specification. A higher V_{ID} is acceptable as long as the V_{IN} specification is also met.

Table 18: **Complementary Differential SelectIO DC Input and Output Levels for HD I/O Banks**

I/O Standard	V_{ICM} (V)(1)			V_{ID} (V)(2)		V_{OL} (V)(3)	V_{OH} (V)(4)	I_{OL}	I_{OH}
	Min	Typ	Max	Min	Max	Max	Min	mA	mA
DIFF_HSTL_I	0.300	0.750	1.125	0.100	–	0.400	V_{CCO} – 0.400	8.0	–8.0
DIFF_HSTL_I_18	0.300	0.900	1.425	0.100	–	0.400	V_{CCO} – 0.400	8.0	–8.0
DIFF_HSUL_12	0.300	0.600	0.850	0.100	–	20% V_{CCO}	80% V_{CCO}	0.1	–0.1
DIFF_SSTL12	0.300	0.600	0.850	0.100	–	(V_{CCO}/2) – 0.150	(V_{CCO}/2) + 0.150	14.25	–14.25
DIFF_SSTL135	0.300	0.675	1.000	0.100	–	(V_{CCO}/2) – 0.150	(V_{CCO}/2) + 0.150	8.9	–8.9
DIFF_SSTL135_II	0.300	0.675	1.000	0.100	–	(V_{CCO}/2) – 0.150	(V_{CCO}/2) + 0.150	13.0	–13.0
DIFF_SSTL15	0.300	0.750	1.125	0.100	–	(V_{CCO}/2) – 0.175	(V_{CCO}/2) + 0.175	8.9	–8.9
DIFF_SSTL15_II	0.300	0.750	1.125	0.100	–	(V_{CCO}/2) – 0.175	(V_{CCO}/2) + 0.175	13.0	–13.0
DIFF_SSTL18_I	0.300	0.900	1.425	0.100	–	(V_{CCO}/2) – 0.470	(V_{CCO}/2) + 0.470	8.0	–8.0
DIFF_SSTL18_II	0.300	0.900	1.425	0.100	–	(V_{CCO}/2) – 0.600	(V_{CCO}/2) + 0.600	13.4	–13.4

Notes:

1. V_{ICM} is the input common mode voltage.
2. V_{ID} is the input differential voltage.
3. V_{OL} is the single-ended low-output voltage.
4. V_{OH} is the single-ended high-output voltage.

Table 19: **Complementary Differential SelectIO DC Input and Output Levels for HP I/O Banks(1)**

I/O Standard	V_{ICM} (V)(2)			V_{ID} (V)(3)		V_{OL} (V)(4)	V_{OH} (V)(5)	I_{OL}	I_{OH}
	Min	Typ	Max	Min	Max	Max	Min	mA	mA
DIFF_HSTL_I	0.680	$V_{CCO}/2$	$(V_{CCO}/2) + 0.150$	0.100	–	0.400	$V_{CCO} - 0.400$	5.8	–5.8
DIFF_HSTL_I_12	$0.400 \times V_{CCO}$	$V_{CCO}/2$	$0.600 \times V_{CCO}$	0.100	–	$0.250 \times V_{CCO}$	$0.750 \times V_{CCO}$	4.1	–4.1
DIFF_HSTL_I_18	$(V_{CCO}/2) - 0.175$	$V_{CCO}/2$	$(V_{CCO}/2) + 0.175$	0.100	–	0.400	$V_{CCO} - 0.400$	6.2	–6.2
DIFF_HSUL_12	$(V_{CCO}/2) - 0.120$	$V_{CCO}/2$	$(V_{CCO}/2) + 0.120$	0.100	–	$20\% V_{CCO}$	$80\% V_{CCO}$	0.1	–0.1
DIFF_SSTL12	$(V_{CCO}/2) - 0.150$	$V_{CCO}/2$	$(V_{CCO}/2) + 0.150$	0.100	–	$(V_{CCO}/2) - 0.150$	$(V_{CCO}/2) + 0.150$	8.0	–8.0
DIFF_SSTL135	$(V_{CCO}/2) - 0.150$	$V_{CCO}/2$	$(V_{CCO}/2) + 0.150$	0.100	–	$(V_{CCO}/2) - 0.150$	$(V_{CCO}/2) + 0.150$	9.0	–9.0
DIFF_SSTL15	$(V_{CCO}/2) - 0.175$	$V_{CCO}/2$	$(V_{CCO}/2) + 0.175$	0.100	–	$(V_{CCO}/2) - 0.175$	$(V_{CCO}/2) + 0.175$	10.0	–10.0
DIFF_SSTL18_I	$(V_{CCO}/2) - 0.175$	$V_{CCO}/2$	$(V_{CCO}/2) + 0.175$	0.100	–	$(V_{CCO}/2) - 0.470$	$(V_{CCO}/2) + 0.470$	7.0	–7.0

Notes:

1. DIFF_POD10 and DIFF_POD12 HP I/O bank specifications are shown in Table 20, Table 21, and Table 22.
2. V_{ICM} is the input common mode voltage.
3. V_{ID} is the input differential voltage.
4. V_{OL} is the single-ended low-output voltage.
5. V_{OH} is the single-ended high-output voltage.

Table 20: **DC Input Levels for Differential POD10 and POD12 I/O Standards(1)(2)**

I/O Standard	V_{ICM} (V)			V_{ID} (V)	
	Min	Typ	Max	Min	Max
DIFF_POD10	0.63	0.70	0.77	0.14	–
DIFF_POD12	0.76	0.84	0.92	0.16	–

Notes:

1. Tested according to relevant specifications.
2. Standards specified using the default I/O standard configuration. For details, see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).

Table 21: **DC Output Levels for Single-ended and Differential POD10 and POD12 Standards(1)(2)**

Symbol	Description	V_{OUT}	Min	Typ	Max	Units
R_{OL}	Pull-down resistance.	V_{OM_DC} (as described in Table 22)	36	40	44	Ω
R_{OH}	Pull-up resistance.	V_{OM_DC} (as described in Table 22)	36	40	44	Ω

Notes:

1. Tested according to relevant specifications.
2. Standards specified using the default I/O standard configuration. For details, see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).

Table 22: **Table 21 Definitions for DC Output Levels for POD Standards**

Symbol	Description	All Speed Grades	Units
V_{OM_DC}	DC output Mid measurement level (for IV curve linearity).	$0.8 \times V_{CCO}$	V

LVDS DC Specifications (LVDS_25)

The LVDS_25 standard is available in the HD I/O banks. See the *UltraScale Architecture SelectIO Resources User Guide* (UG571) for more information.

Table 23: **LVDS_25 DC Specifications**

Symbol	DC Parameter	Min	Typ	Max	Units
V_{CCO}(1)	Supply voltage.	2.375	2.500	2.625	V
V_{IDIFF}	Differential input voltage: ($\underline{Q}$ – $\overline{Q}$), $\underline{Q}$ = High ($\overline{Q}$ – Q), $\overline{Q}$ = High	100	350	600(2)	mV
V_{ICM}	Input common-mode voltage.	0.300	1.200	1.425	V

Notes:

1. LVDS_25 in HD I/O banks supports inputs only. LVDS_25 inputs without internal termination have no V_{CCO} requirements. Any V_{CCO} can be chosen as long as the input voltage levels do not violate the *Recommended Operating Condition* (Table 2) specification for the V_{IN} I/O pin voltage.
2. Maximum V_{IDIFF} value is specified for the maximum V_{ICM} specification. With a lower V_{ICM}, a higher V_{DIFF} is tolerated only when the recommended operating conditions and overshoot/undershoot V_{IN} specifications are maintained.

LVDS DC Specifications (LVDS)

The LVDS standard is available in the HP I/O banks. See the *UltraScale Architecture SelectIO Resources User Guide* (UG571) for more information.

Table 24: **LVDS DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO}(1)	Supply voltage.		1.710	1.800	1.890	V
V_{ODIFF}(2)	Differential output voltage: ($\underline{Q}$ – $\overline{Q}$), $\underline{Q}$ = High ($\overline{Q}$ – Q), $\overline{Q}$ = High	R_T = 100Ω across Q and $\overline{Q}$ signals	247	350	454	mV
V_{OCM}(2)	Output common-mode voltage.	R_T = 100 Ω across Q and $\overline{Q}$ signals	1.000	1.250	1.425	V
V_{IDIFF}(3)	Differential input voltage: ($\underline{Q}$ – $\overline{Q}$), $\underline{Q}$ = High ($\overline{Q}$ – Q), $\overline{Q}$ = High		100	350	600(3)	mV
V_{ICM_DC}(4)	Input common-mode voltage (DC coupling).		0.300	1.200	1.425	V
V_{ICM_AC}(5)	Input common-mode voltage (AC coupling).		0.600	–	1.100	V

Notes:

1. In HP I/O banks, when LVDS is used with input-only functionality, it can be placed in a bank where the V_{CCO} levels are different from the specified level only if internal differential termination is not used. In this scenario, V_{CCO} must be chosen to ensure the input pin voltage levels do not violate the *Recommended Operating Condition* (Table 2) specification for the V_{IN} I/O pin voltage.
2. V_{OCM} and V_{ODIFF} values are for LVDS_PRE_EMPHASIS = FALSE.
3. Maximum V_{IDIFF} value is specified for the maximum V_{ICM} specification. With a lower V_{ICM}, a higher V_{DIFF} is tolerated only when the recommended operating conditions and overshoot/undershoot V_{IN} specifications are maintained.
4. Input common mode voltage for DC coupled configurations. EQUALIZATION = EQ_NONE (Default).
5. External input common mode voltage specification for AC coupled configurations. EQUALIZATION = EQ_LEVEL0, EQ_LEVEL1, EQ_LEVEL2, EQ_LEVEL3, EQ_LEVEL4.

AC Switching Characteristics

All values represented in this data sheet are based on the speed specifications in the Vivado® Design Suite as outlined in Table 25.

Table 25: **Speed Specification Version By Device**

2017.1	Device
1.08	XCZU4CG, XCZU4EG, XCZU4EV, XCZU5CG, XCZU5EG, XCZU5EV, XCZU11EG
1.10	XCZU2CG, XCZU2EG, XCZU3CG, XCZU3EG, XCZU6CG, XCZU6EG, XCZU7CG, XCZU7EG, XCZU7EV, XCZU9CG, XCZU9EG, XCZU15EG, XCZU17EG, XCZU19EG

Switching characteristics are specified on a per-speed-grade basis and can be designated as Advance, Preliminary, or Production. Each designation is defined as follows:

Advance Product Specification

These specifications are based on simulations only and are typically available soon after device design specifications are frozen. Although speed grades with this designation are considered relatively stable and conservative, some under-reporting might still occur.

Preliminary Product Specification

These specifications are based on complete ES (engineering sample) silicon characterization. Devices and speed grades with this designation are intended to give a better indication of the expected performance of production silicon. The probability of under-reporting delays is greatly reduced as compared to Advance data.

Product Specification

These specifications are released once enough production silicon of a particular device family member has been characterized to provide full correlation between specifications and devices over numerous production lots. There is no under-reporting of delays, and customers receive formal notification of any subsequent changes. Typically, the slowest speed grades transition to production before faster speed grades.

Testing of AC Switching Characteristics

Internal timing parameters are derived from measuring internal test patterns. All AC switching characteristics are representative of worst-case supply voltage and junction temperature conditions.

For more specific, more precise, and worst-case guaranteed data, use the values reported by the static timing analyzer and back-annotate to the simulation net list. Unless otherwise noted, values apply to all Zynq UltraScale+ MPSoC.

Speed Grade Designations

Since individual family members are produced at different times, the migration from one category to another depends completely on the status of the fabrication process for each device. Table 26 correlates the current status of the Zynq UltraScale+ MPSoC on a per speed grade basis. See Table 3 for operating voltages listed by speed grade.

Table 26: **Speed Grade Designations by Device**

Device	Speed Grade, Temperature Ranges, and V_{CCINT} Operating Voltages		
	Advance	Preliminary	Production
XCZU2CG	-2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCZU2EG	-2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCZU3CG	-2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCZU3EG	-2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCZU4CG	-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU4EG	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU4EV	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU5CG	-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		

Table 26: **Speed Grade Designations by Device *(Cont'd)***

Device	Speed Grade, Temperature Ranges, and V_{CCINT} Operating Voltages		
	Advance	**Preliminary**	**Production**
XCZU5EG	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU5EV	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU6CG	-2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCZU6EG	-3E (V_{CCINT} = 0.90V) -2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCZU7CG	-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU7EG	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU7EV	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU9CG	-2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCZU9EG	-3E (V_{CCINT} = 0.90V) -2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)

Table 26: **Speed Grade Designations by Device *(Cont'd)***

Device	Speed Grade, Temperature Ranges, and V_{CCINT} Operating Voltages		
	Advance	**Preliminary**	**Production**
XCZU11EG	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU15EG	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU17EG	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU19EG	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		

Notes:

1. The lowest power -1L and -2L devices, where V_{CCINT} = 0.72V, are listed in the Vivado Design Suite as -1LV and -2LV respectively.